

RF POWER TRANSISTOR

DESCRIPTION:

The **ASI 1214-6** is a Common Base Transistor Designed for Long Pulse High Reliability L-Band Radar Applications.

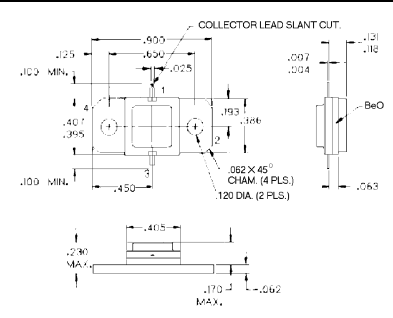
FEATURES INCLUDE:

- Gold Metallization
- Hermetic Package
- Input/Output Matching

MAXIMUM RATINGS

I_C	5.0 A
V_{CB}	55 V
P_{DISS}	125 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	1.4 °C/W

PACKAGE - .400 x .400 2NLFL



1 = COLLECTOR
3 = EMITTER 2 & 4 = BASE

	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm
		.055/.140	K	.002/.005	.005/.015
B	.120/.305	.130/.330	L	.055/.140	.065/.165
C		.785/.19.54	M	.080/.203	.095/.241
D	.455/.11.56	.465/.11.81	N		.195/.4.93
E	.130/.3.30		P	.455/.11.56	.468/.11.89
F	.230/.5.84				
G	.100/.3.25				
H	.838/.21.28	.850/.21.59			
I	1.995/.27.81	1.105/.28.07			
J	.525/.13.34	.535/.13.59			

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 20 mA	55			V
BV_{CER}	I _C = 40 mA R _{BE} = 10 Ω	55			V
BV_{EBO}	I _E = 2.0 mA	3.5			V
I_{CES}	V _{CE} = 28 V			10	mA
h_{FE}	V _{CE} = 5.0 V I _C = 2.0 A	15		150	---
P_G	V _{CC} = 28 V P _{OUT} = 55 W f = 1214 to 1400 MHz	6.6	7.2		dB
η_C	Pulse Width = 1000 μS Duty Cycle = 10%	50	55		%